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2N6469 Silicon P-N-P

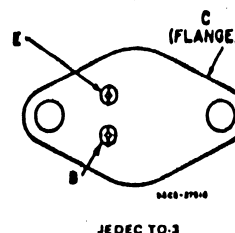
Maximum Ratings, Absolute-Maximum Values:

*COLLECTOR-TO-BASE VOLTAGE	V _{CB0}	50	V
COLLECTOR-TO-EMITTER VOLTAGE:			
• With external base-to-emitter resistance (R _{BE}) = 100 Ω	V _{CER}	50	V
With base open	V _{CEO}	40	V
*EMITTER-TO-BASE VOLTAGE	V _{EB0}	5	V
*CONTINUOUS COLLECTOR CURRENT	I _C	15	A
*CONTINUOUS BASE CURRENT	I _B	5	A
*TRANSISTOR DISSIPATION:	P _T		
At case temperatures up to 25°C		125	W
At case temperatures above 25°C		← Derate linearly 200°C →	
*TEMPERATURE RANGE:			
Storage & Operating (Junction)		← -65 to +200 →	°C
*PIN TEMPERATURE (During Soldering):			
At distances > 1/32" (0.8 mm) from seating plane for 10 s max.		← +235 →	°C

* In accordance with JEDEC registration data format (JES-6 RDP-2).

For p-n-p devices, voltage and current values are negative.

TERMINAL DESIGNATIONS



ELECTRICAL CHARACTERISTICS FOR

At case temperature (T_C) = 25°C unless otherwise specified

SYMBOL	TEST CONDITIONS				LIMITS		UNITS
	VOLTAGE V dc		CURRENT A dc		2N6469		
	V _{CE}	V _{BE}	I _C	I _B	Min.	Max.	
I _{CER} (R _{BE}) = 100 Ω	-35				-	-200	μA
I _{CEX}	-45	1.5			-	-200	μA
T _C = 160°C	-45	1.5			-	-5	mA
I _{CEO}	-20			0 0	- -	-1	mA
I _{EBO}		5		0	-	-5	mA
h _{FE}	-4		-5 ^a		20	150	
	-4		-15 ^a		5	-	
V _{CEO(1us)}			-0.2	0	-40 ^b	-	V
V _{CER(1us)}			-0.2		-50 ^b	-	
V _{BE}	-4		-15 ^a		-	-3.5	V
	-4		-7 ^a		-	-	
V _{CE(sat)}			-5 ^a	-0.5	-	-1.3	V
			-15 ^a	-5	-	-3.5	
					-	-	
h _{ie} f = 2 MHz	-4		-1		5	-	
h _{ie} f = 1 kHz	-4		-1		25	-	
R _{θJC}					-	1.4	°C/W

* In accordance with JEDEC registration data format (JES-6 RDP-2).

^a Pulsed; pulse duration = 300 μs, duty factor = 1.0%.

^b CAUTION: Sustaining voltages V_{CEO(1us)} and V_{CER(1us)} MUST NOT be measured on a curve tracer.